ON Semiconductor®

FDD3670

100V N-Channel PowerTrench® MOSFET

General Description

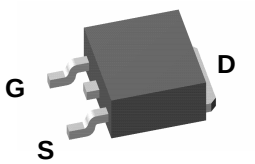
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs f eature faster switching and lower gate charge than other MOSFETs with comparable $R_{DS(ON)}$ specifications.

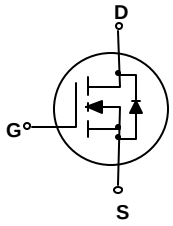
The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 34 A, 100 V. $R_{DS(ON)}$ = 32 mΩ @ V_{GS} = 10 V
  $R_{DS(ON)}$ = 35 mΩ @ V_{GS} = 6 V
- Low gate charge (57 nC typical)
- Fast switching speed
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability



TO-252



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		100	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Drain Current – Continuous	(Note 1)	34	A
	Drain Current – Pulsed	(Note 3)	100	
P_D	Maximum Power Dissipation @ T_C = 25°C	(Note 1)	83	W
	@ T_A = 25°C	(Note 1a)	3.8	
	@ T_A = 25°C	(Note 1b)	1.6	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		–55 to +175	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	1.8	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1b)	96	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDD3670	FDD3670	13”	16mm	2500 units

November-2017, Rev. 2

Publication Order Number:
FDD3670/D

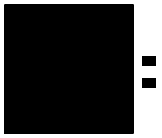
Electrical Characteristics

T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Drain-Source Avalanche Ratings (Note 2)						
W_{DSS}	Single Pulse Drain-Source Avalanche Energy	V_{DD} = 50 V, I_D = 7.3 A			360	mJ
I_{AR}	Maximum Drain-Source Avalanche Current				7.3	A
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C		92		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80 V, V_{GS} = 0 V			10	μA
I_{GSSF}	Gate–Body Leakage, Forward	V_{GS} = 20 V, V_{DS} = 0 V			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	V_{GS} = –20 V, V_{DS} = 0 V			–100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	2	2.5	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C		–7.2		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	V_{GS} = 10 V, I_D = 7.3 A V_{GS} = 10 V, I_D = 7.3 A, T_J = 125°C V_{GS} = 6 V, I_D = 7.0 A		22 39 24	32 56 35	mΩ
$I_{D(on)}$	On–State Drain Current	V_{GS} = 10 V, V_{DS} = 5 V	25			A
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 7.3 A	15	31		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 50 V, V_{GS} = 0 V, f = 1.0 MHz		2490		pF
C_{oss}	Output Capacitance			265		pF
C_{rss}	Reverse Transfer Capacitance			80		pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = 50 V, I_D = 1 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		16	26	ns
t_r	Turn–On Rise Time			10	18	ns
$t_{d(off)}$	Turn–Off Delay Time			56	84	ns
t_f	Turn–Off Fall Time			25	40	ns
Q_g	Total Gate Charge	V_{DS} = 50 V, I_D = 7.3 A, V_{GS} = 10 V		57	80	nC
Q_{gs}	Gate–Source Charge			11		nC
Q_{gd}	Gate–Drain Charge			15		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				2.7	A
V_{SD}	Drain–Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 2.7 A (Note 2)		0.72	1.2	V

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) $R_{\theta JA}$= 40°C/W when mounted on a 1in^2 pad of 2oz copper.

b) $R_{\theta JA}$= 96°C/W on a minimum mounting pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300μs, Duty Cycle < 2.0%

3. Pulse Id refers to Figure.9 Forward Bias Safe Operation Area.

Typical Characteristics

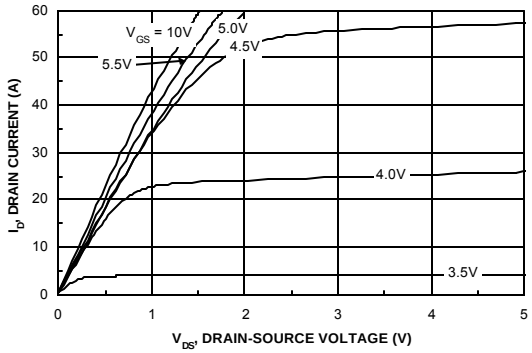


Figure 1. On-Region Characteristics.

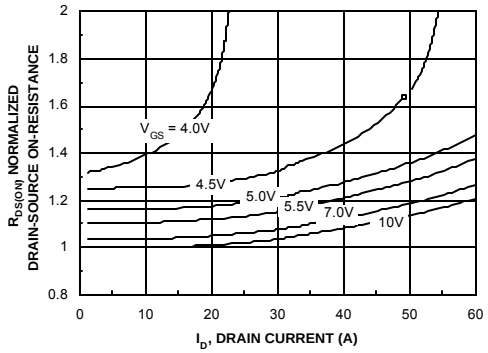


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

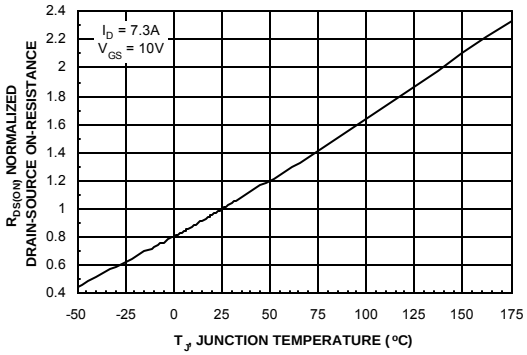


Figure 3. On-Resistance Variation with Temperature.

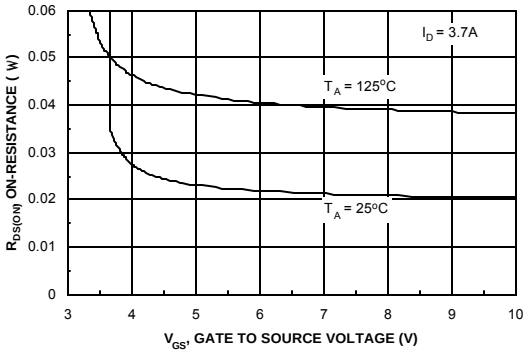


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

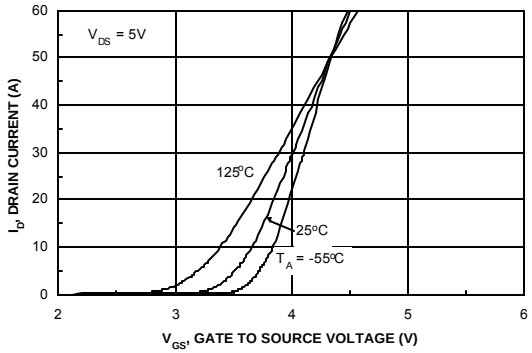


Figure 5. Transfer Characteristics.

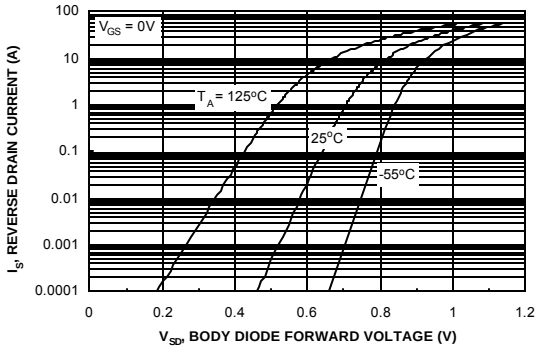


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

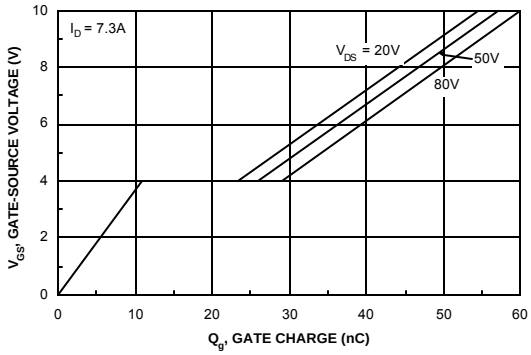


Figure 7. Gate Charge Characteristics.

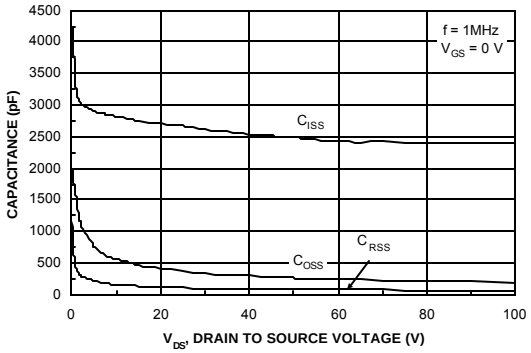


Figure 8. Capacitance Characteristics.

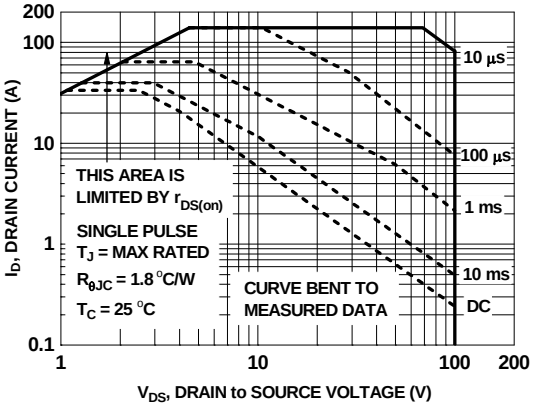


Figure 9. Forward Bias Safe Operating Area.

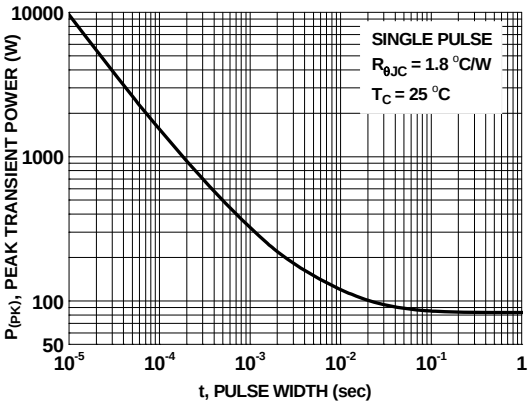


Figure 10. Single Pulse Maximum Power Dissipation.

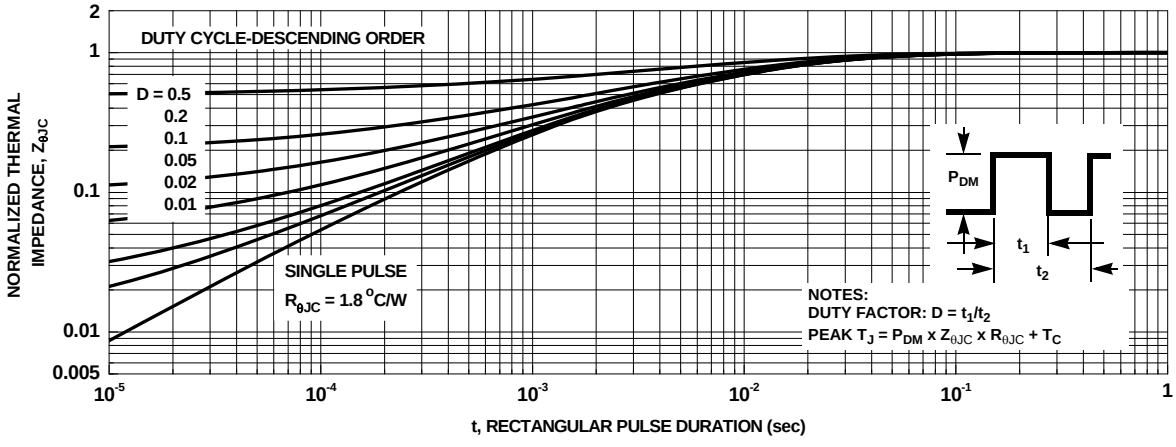


Figure 11. Junction-to-Case Transient Thermal Response Curve

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative